Electronic Supplementary Material (ESI) for Nanoscale Advances.

n/p-doping in buckled honeycomb InAs monolayer using IVA-group impurities

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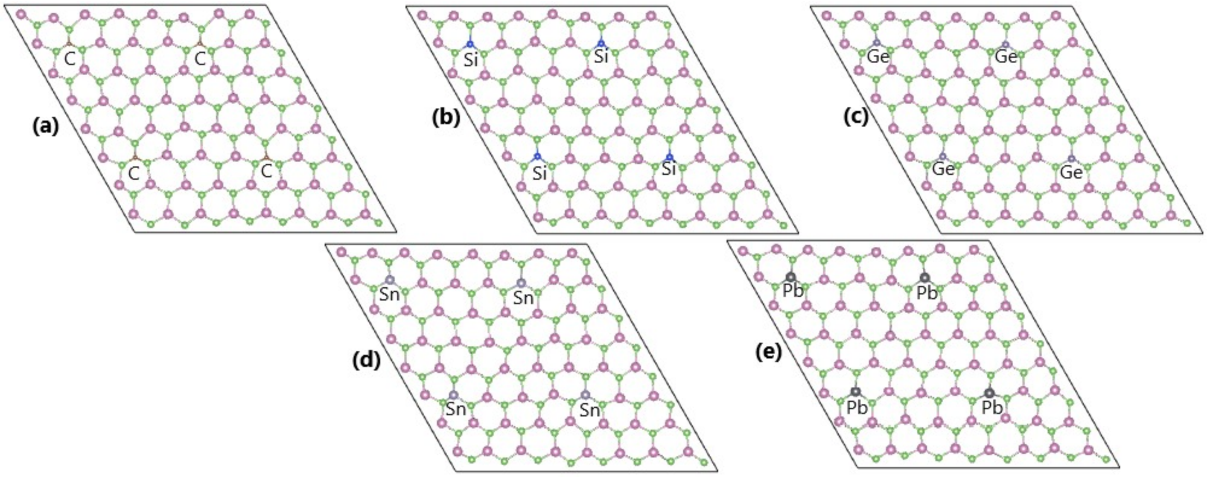

Figure S1: Atomic structure of InAs monolayer with (a) C_{In}, (b) Si_{In}, (c) Ge_{In}, (d) Sn_{In}, and (e) Pb_{In} doping after AIMD simulations.

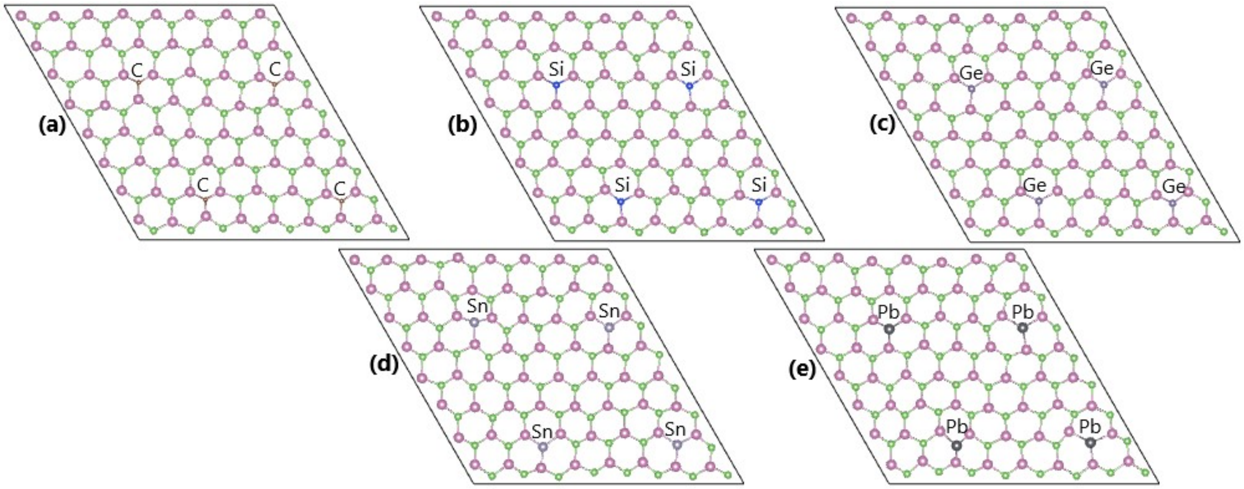

Figure S2: Atomic structure of InAs monolayer with (a) C_{As}, (b) Si_{As}, (c) Ge_{As}, (d) Sn_{As}, and (e) Pb_{As} doping after AIMD simulations.